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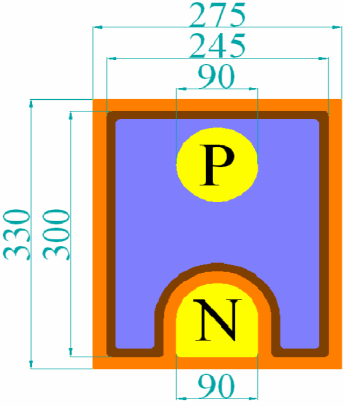
Data Sheet

LED Chip green

EOLC-515-35

Rev. 02, 2017

Radiation	Type	Electrodes
green	InGaN/GaN	P + N up

	Description - Chip size: $330 \pm 20 \mu\text{m} \times 275 \pm 20 \mu\text{m}$ (13 x 11 mil) - P-bonding pad: $\varnothing 90 \pm 10 \mu\text{m}$, thickness $2 \pm 0.2 \mu\text{m}$, Au - N-bonding pad: $\varnothing 90 \pm 10 \mu\text{m}$, thickness $2 \pm 0.2 \mu\text{m}$, Au - Chip thickness: $90 \pm 10 \mu\text{m}$
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Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			30	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$	I_{FM}			100	mA

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 1 \mu\text{A}$	V_F	1.7			V
Forward voltage	$I_F = 20 \text{ mA}$	V_F	2.8		3.8	V
Reverse current	$V_R = 8 \text{ V}$	I_R			0.5	μA
Dominant wavelength	$I_F = 20 \text{ mA}$	λ_D		515		nm
Luminous intensity	$I_F = 20 \text{ mA}$	I_v	485		530	mcd

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 132



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.